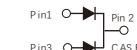


FEATURES

- Power pack
- Metal silicon junction ,majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss ,high efficiency
- High current capability ,low forward voltage drop
- High forward surge capability
- High frequency operation
- Meets MSL Level 1, per J-STD-020,LF MAX peak of 245°C (for TO-263 package)
- Solder bath temperature 275°C maximum, 10s, per JESD22-B106 (for TO-220AB and ITO-220AB package)
- Component in accordance to RoHS 2011/65/EU



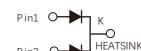
TO-220AB



ITO-220AB



TO-263



MECHANICAL DATA

- Case: JEDEC TO-220AB、ITO-220AB、TO-263
- Molding compound meets UL94V-0 flammability rating
- Terminals: Lead solderable per J-STD-002 and JESD22-B102
- Polarity: As marked
- Mounting Torque: 10 in-lbs maximum

TYPICAL APPLICATIONS

For use in low voltage ,high frequency inverters ,DC/DC converters,free wheeling ,and polarity protection applications

PRIMARY CHARACTERISTICS	
I _{F(AV)}	2x30A
V _{RRM}	100V
I _{FSM}	300A
V _r at I _f =30.0A,Per leg,T _j =125°C	0.68V,Typ
I _{stg} ,T _j =25°C	15µA Typ
T _(MAX)	150°C
Package	TO-220AB,ITO-220AB, TO-263
Diode variations	Common cathode

MAXIMUM RATINGS

(Ratings at 25°C ambient temperature unless otherwise specified)

Parameter	Symbol	Value	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	100	V
Maximum average forward rectified current (see fig.1)	I _{F(AV)}	30.0	A
		60.0	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method at rated TL)	I _{FSM}	300	A
Peak repetitive reverse current per diode at tp=2µs 1KHz	I _{RRM}	0.5	A
Storage temperature range	T _{stg}	-55 to +150	°C
Operating junction temperature range	T _j	-55 to +150	°C

RATINGS AND CHARACTERISTIC OF SR60100LCT,SRF60100LCT,SR60100LD1

ELECTRICAL CHARACTERISTICS (T_A=25°C Unless otherwise noted)

Parameter	Test Conditions		Symbol	Typ.	Max.	Unit
Instantaneous forward voltage	T _j =25°C	I _F =5.0A	V _F ¹⁾	0.44	-	V
		I _F =10.0A		0.52	-	
		I _F =15.0A		0.59	-	
		I _F =20.0A		0.66	-	
		I _F =30.0A		0.76	0.80	
	T _j =125°C	I _F =5.0A		0.35	-	
		I _F =10.0A		0.48	-	
		I _F =15.0A		0.56	-	
		I _F =20.0A		0.61	-	
		I _F =30.0A		0.68	0.72	
Reverse current	VR=100V	T _A =25°C	I _R ²⁾	15	50	μA
		T _A =100°C		3.5	-	mA
		T _A =125°C		15	-	
Typical junction capacitance	4V,1MHz		C _J	1200		pF

Notes: 1. Pulse test: 300 μs pulse width, 1% duty cycle

2. Pulse test: pulse width ≤ 40ms

THERMAL CHARACTERISTICS

Parameter	Symbol	TO-220AB	ITO-220AB	TO-263	Unit
Typical thermal resistance ³⁾	R _{θJC}	0.5	1.5	0.5	°C/W

3. Thermal resistance from junction to case

AVAILABALE PACK INFORMATION

Product code	Pack	Box Size L×W×H(mm)	Quantity(pcs/box)	Carton SizeL×W×H(mm)	Quantity(box/carton)
SR60100LCT-TO-220AB	P/T	558×148×38	1000	565×225×170	5
SRF60100LCT-ITO-220AB	P/T	558×148×38	1000	565×225×170	5
SR60100LD1-TO-263	P/T	558×148×38	1000	565×225×170	5

RATINGS AND CHARACTERISTIC OF SR60100LCT,SRF60100LCT,SR60100LD1

FIG.1-FORWARD CURRENT DERATING CURVE

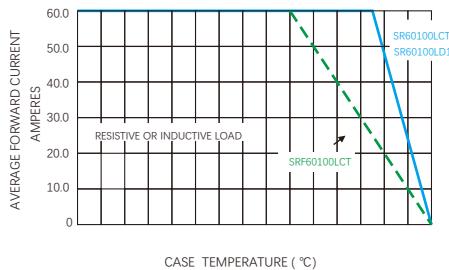


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

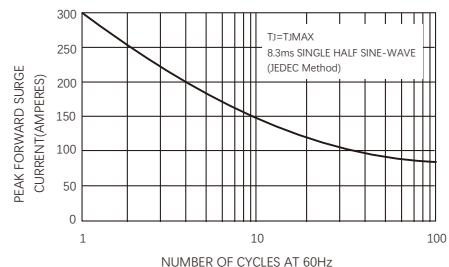


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

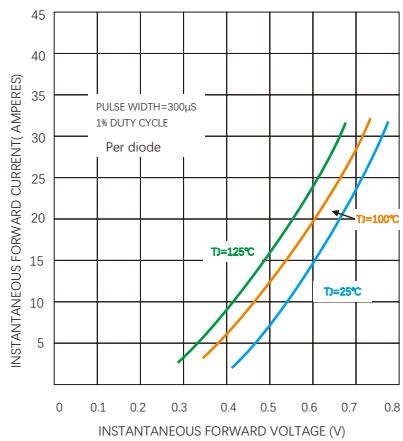


FIG.4-TYPICAL REVERSE CHARACTERISTICS

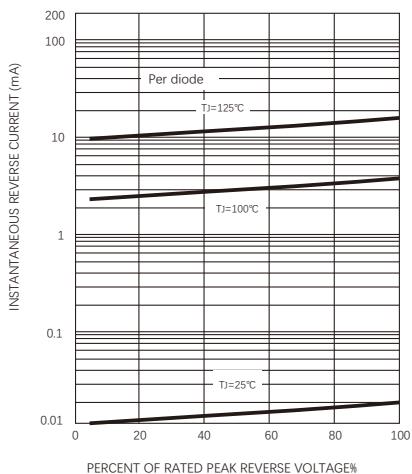
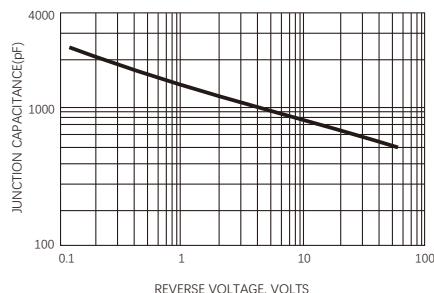
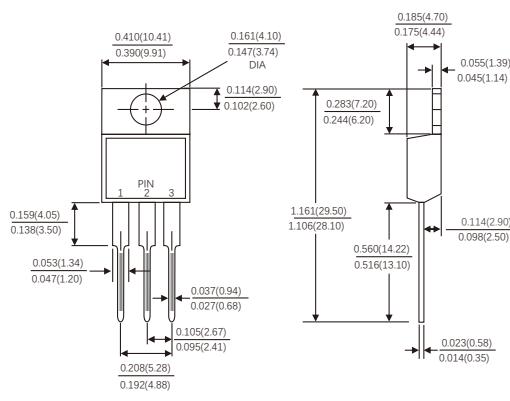


FIG.5-TYPICAL JUNCTION CAPACITANCE

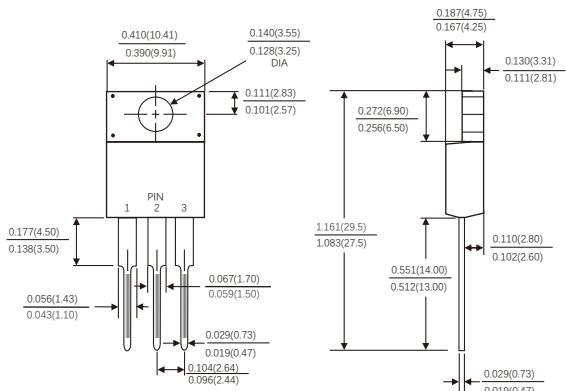


PACKAGE OUTLINE DIMENSIONS

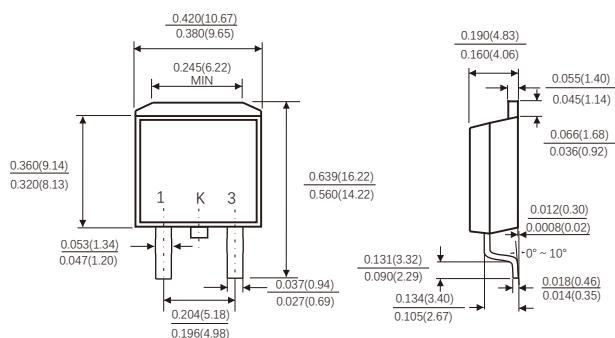
TO-220AB



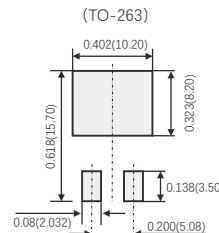
ITO-220AB



TO-263



Suggested Pad Layout



(设计者可参考推荐值根据焊接工艺
要求自行确定适合的焊盘尺寸)
(Designers can refer to the recommended
values according to the manufacturing process
requirements to determine the appropriate pad size.)

Dimensions in inches and (millimeters)